

**A SEMICONDUCTOR DEVICE HAVING A SILICIDED
GATE ELECTRODE AND METHOD OF MANUFACTURE THEREFOR**

ABSTRACT OF THE DISCLOSURE

The present invention provides a semiconductor device, a method of manufacture therefor, and a method for manufacturing an integrated circuit. The semiconductor device (100), among other possible elements, includes a silicided gate electrode (150) located over a substrate (110), the silicided gate electrode (150) having gate sidewall spacers (160) located on sidewalls thereof. The semiconductor device (100) further includes source/drain regions (170) located in the substrate (110) proximate the silicided gate electrode (150), and silicided source/drain regions (180) located in the source/drain regions (170) and at least partially under the gate sidewall spacers (160).